

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

B. Amendments to the Specification.

Please replace the paragraph starting at Page 2, Line 19, with the following.

5 A conventional plasma chamber part cleaning process will now be described with reference to FIG. 5. A conventional chamber part cleaning process 500 may include an initial wet chemical cleaning (step 502). For example, chamber equipment may be submerged in a mixture of hydrogen peroxide (H_2O_2) and ammonium hydroxide (NH_4OH). More particularly, chamber equipment may be submerged in a 30% solution of H_2O_2 in a
10 1:1 ratio with $[[NH_4OH]]$ NH_4OH for about 20 minutes.

Please replace the paragraph starting at Page 3, Line 8, with the following.

15 A drawback to a conventional method 500 can be how such a cleaning method affects chamber part surfaces. For example, chamber parts can typically be formed from quartz. A wet clean of H_2O_2 and $[[NH_4OH]]$ NH_4OH may etch quartz surfaces changing surface textures. Changes in chamber part surfaces may result in drift in an etch process, as a changing surface conditions may alter gas flows and or etch chemistry. Further, because cleaning may consume etch chamber parts, such parts may have to be periodically replaced.

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Please replace the paragraph starting at Page 8, Line 15, with the following.

25 Plasma cleaning with oxygen as a source gas (also referred to "ashing") can remove organic based materials, such a polymer-based photoresist. At the same time, an oxygen plasma etch can leave quartz surfaces essentially unaltered. In this way, unlike conventional cleaning methods that may consume quartz material in an H_2O_2 and $[[NH_4OH]]$ NH_4OH dip, a third embodiment 300 may clean quartz material with a solvent and/or plasma clean that consumes essentially
30 no quartz material.

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